[Claims]

[Claim 1]

Etchant composition for batch etching treatment of tungsten film and titanium nitride film comprising a nitric acid, water, a phosphoric acid and at least one selected from the group consisting of a sulfuric acid and an aliphatic sulfonic acid, wherein the sulfuric acid is in an amount between 11.73 and 40.0 wt % and the aliphatic sulfonic acid is in an amount between 17.71 and 40.0 wt%.

[Claim 2]

The etchant composition according to Claim 1, wherein the etchant composition comprises a methanesulfonic acid.

[Claim 3]

Method for batch etching of tungsten film and titanium nitride film using the etchant composition according to any one of Claims 1 to 2.

[Claim 4]

The method according to Claim 3, wherein the temperature of the etching composition at which the etching is performed is 50 °Cor higher.

[Claim 5]

The method according to Claim 3 or 4 for generating a pattern having a three-dimensional structure.